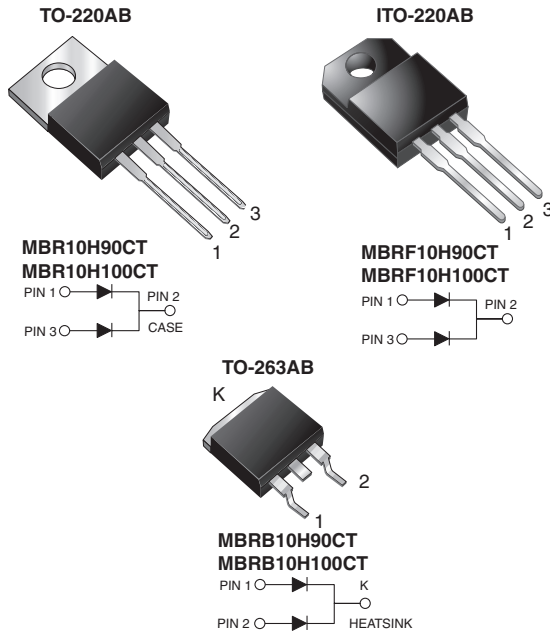


Dual Common-Cathode High-Voltage Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance



FEATURES

- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder Dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	5 A x 2
V_{RRM}	90 V, 100 V
I_{FSM}	150 A
V_F	0.61 V
I_R	3.5 μ A
T_J max.	175 °C

MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	MBR10H90CT	MBR10H100CT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	90	100	V
Working peak reverse voltage	V_{RWM}	90	100	V
Maximum DC blocking voltage	V_{DC}	90	100	V
Maximum average forward rectified current at $T_C = 105$ °C total device per diode	$I_{F(AV)}$	10 5.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	150		A
Peak repetitive reverse current per diode at $t_p = 2$ μ s, 1 kHz	I_{RRM}	0.5		A
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μ s
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 175		°C
Isolation voltage (ITO-220AB only) from terminals to heatsink t = 1 min	V_{AC}	1500		V

MBR(F,B)10H90CT & MBR(F,B)10H100CT

Vishay General Semiconductor



ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	I _F = 5.0 A	T _J = 25 °C	V _F	0.76	V
	I _F = 5.0 A	T _J = 125 °C		0.61	
	I _F = 10 A	T _J = 25 °C		0.85	
	I _F = 10 A	T _J = 125 °C		0.71	
Maximum reverse current per diode at working peak reverse voltage ⁽¹⁾			I _R	3.5	μA
				4.5	

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRF	MBRB	UNIT
Typical thermal resistance per diode	R _{θJC}	2.2	5.2	2.2	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	MBR10H100CT-E3/45	1.85	45	50/tube	Tube
ITO-220AB	MBRF10H100CT-E3/45	1.79	45	50/tube	Tube
TO-263AB	MBRB10H100CT-E3/45	1.35	45	50/tube	Tube
TO-263AB	MBRB10H100CT-E3/81	1.35	81	800/reel	Tape reel
TO-220AB	MBR10H100CTHE3/45 ⁽¹⁾	1.85	45	50/tube	Tube
ITO-220AB	MBRF10H100CTHE3/45 ⁽¹⁾	1.79	45	50/tube	Tube
TO-263AB	MBRB10H100CTHE3/45 ⁽¹⁾	1.35	45	50/tube	Tube
TO-263AB	MBRB10H100CTHE3/81 ⁽¹⁾	1.35	81	800/reel	Tape reel

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

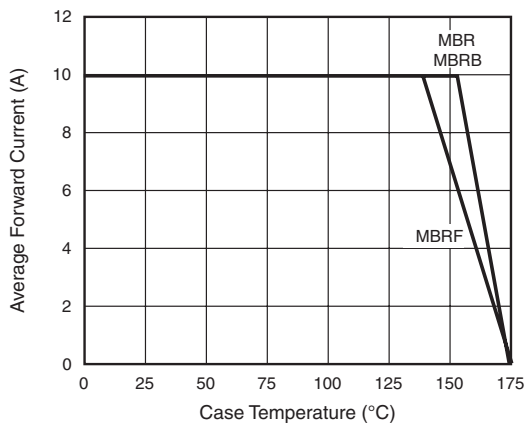


Figure 1. Forward Derating Curve Per Diode

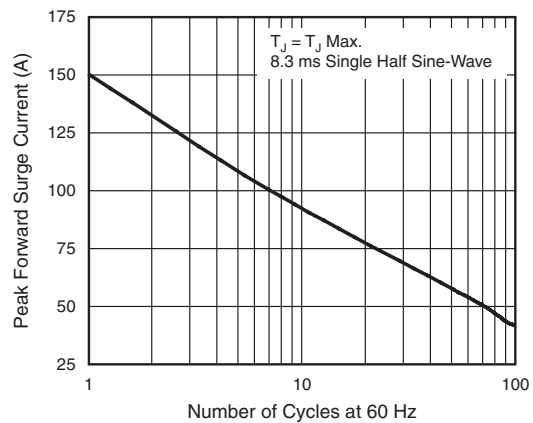


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

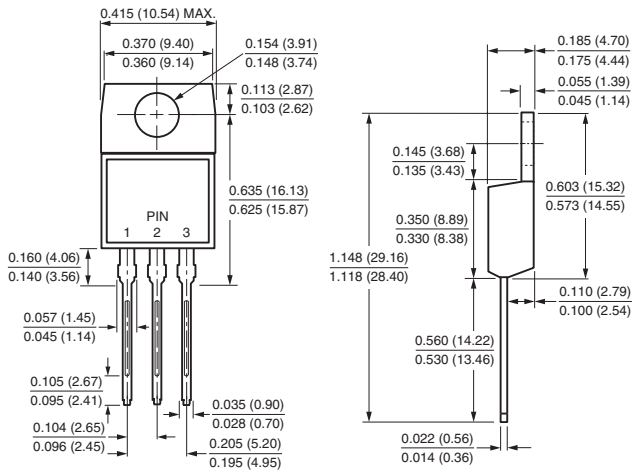
MBR(F,B)10H90CT & MBR(F,B)10H100CT

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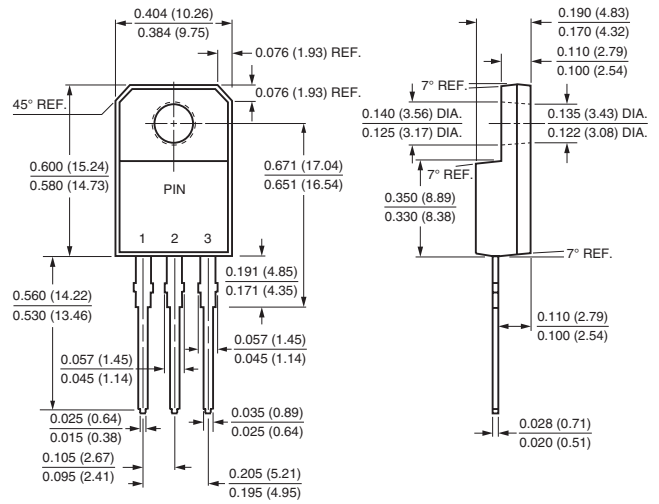


PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

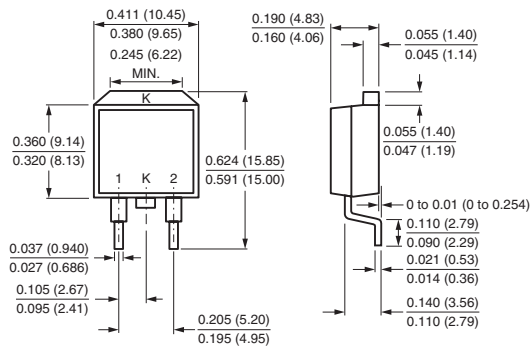
TO-220AB



ITO-220AB



TO-263AB



Mounting Pad Layout

